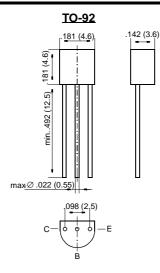
# **BC546 THRU BC549**

## **Small Signal Transistors (NPN)**



Dimensions in inches and (millimeters)

### FEATURES

- NPN Silicon Epitaxial Planar Transistors
- These transistors are subdivided into three groups A, B and C according to their current gain. The type BC546 is available in groups A and B, however, the types BC547 and BC548 can be supplied in all three groups. The BC549 is a low-noise type and available in groups B and C. As complementary types, the PNP transistors BC556 ... BC559 are recommended.
- On special request, these transistors are also manufactured in the pin configuration TO-18.

#### **MECHANICAL DATA**

**Case:** TO-92 Plastic Package **Weight:** approx. 0.18 g

#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

		Symbol	Value	Unit
Collector-Base Voltage	BC546 BC547 BC548, BC549	V <sub>CBO</sub> V <sub>CBO</sub> V <sub>CBO</sub>	80 50 30	V V V
Collector-Emitter Voltage	BC546 BC547 BC548, BC549	V <sub>CES</sub> V <sub>CES</sub> V <sub>CES</sub>	80 50 30	V V V
Collector-Emitter Voltage	BC546 BC547 BC548, BC549	V <sub>CEO</sub> V <sub>CEO</sub> V <sub>CEO</sub>	65 45 30	V V V
Emitter-Base Voltage	BC546, BC547 BC548, BC549	V <sub>EBO</sub> V <sub>EBO</sub>	6 5	V V
Collector Current		I <sub>C</sub>	100	mA
Peak Collector Current		I <sub>CM</sub>	200	mA
Peak Base Current		I <sub>BM</sub>	200	mA
Peak Emitter Current		-I <sub>EM</sub>	200	mA
Power Dissipation at T <sub>amb</sub> = 25 °C		P <sub>tot</sub>	500 <sup>1)</sup>	mW
Junction Temperature		Tj	150	°C
Storage Temperature Range		T <sub>S</sub>	-65 to +150	°C



# BC546 THRU BC549

### ELECTRICAL CHARACTERISTICS

	Symbol	Min.	Тур.	Max.	Unit
h-Parameters at $V_{CE}$ = 5 V, $I_C$ = 2 mA, f = 1 kHz,					
Small Signal Current Gain					
Current Gain Group A	h <sub>fe</sub>	-	220	-	-
В	h <sub>fe</sub>	-	330	-	_
Input Impedance Current Gain Group A	∣ h <sub>fe</sub> ∣ h <sub>ie</sub>	1.6	600 2.7	- 4.5	kΩ
B	h <sub>ie</sub>	3.2	4.5	8.5	kΩ
Č	h <sub>ie</sub>	6	8.7	15	kΩ
Output Admittance Current Gain Group A	h <sub>oe</sub>	_	18	30	μS
В	h <sub>oe</sub>	-	30	60	μS
C C	h <sub>oe</sub>	-	60	110	μS
Reverse Voltage Transfer Ratio Current Gain Group A	h <sub>re</sub>	_	1.5 · 10 <sup>-4</sup>	_	
B	h <sub>re</sub>	_	2 10 <sup>-4</sup>	_	
C	h <sub>re</sub>	_	3 · 10 <sup>-4</sup>	_	-
-					
DC Current Gain					
at $V_{CE} = 5 \text{ V}$ , $I_C = 10\mu\text{A}$ Current Gain Group A	h		90		_
B	h <sub>FE</sub> h <sub>FE</sub>	_	90 150	_	_
č	h <sub>FE</sub>	_	270	_	_
at $V_{CE} = 5 \text{ V}$ , $I_C = 2 \text{ mA}$			-		
Current Gain Group A	h <sub>FE</sub>	110	180	220	-
B C	h <sub>FE</sub>	200	290	450	_
at $V_{CE} = 5 \text{ V}$ , $I_C = 100 \text{ mA}$	h <sub>FE</sub>	420	500	800	-
Current Gain Group A	h <sub>FE</sub>	_	120	_	_
В	h <sub>FE</sub>	_	200	_	_
C	h <sub>FE</sub>	_	400	-	-
Thermal Resistance Junction to Ambient Air	R <sub>thJA</sub>	_	_	250 <sup>1)</sup>	K/W
Collector Saturation Voltage					
at $I_{C} = 10 \text{ mA}$ , $I_{B} = 0.5 \text{ mÅ}$	V <sub>CEsat</sub>	_	80	200	mV
at I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5 mA	V <sub>CEsat</sub>	-	200	600	mV
Base Saturation Voltage					
at $I_C = 10$ mA, $I_B = 0.5$ mA	V <sub>BEsat</sub>	_	700	_	mV
at $I_{C} = 100 \text{ mA}$ , $I_{B} = 5 \text{ mA}$	V <sub>BEsat</sub>	_	900	_	mV
Base-Emitter Voltage at $V_{CE} = 5 \text{ V}, I_C = 2 \text{ mA}$	V <sub>BE</sub>	580	660	700	mV
			000	100	1111
		_	_	720	mV
at $V_{CE} = 5 V$ , $I_C = 10 mA$	VBE VBE	_	-	720	mV
at $V_{CE} = 5$ V, $I_C = 10$ mA Collector-Emitter Cutoff Current	V <sub>BE</sub>	_	-		
at $V_{CE} = 5 \text{ V}$ , $I_C = 10 \text{ mA}$ Collector-Emitter Cutoff Current at $V_{CE} = 80 \text{ V}$ BC546	V <sub>BE</sub>		- 0.2	15	nA
at $V_{CE} = 5$ V, $I_C = 10$ mA Collector-Emitter Cutoff Current	V <sub>BE</sub>	- - -	- 0.2 0.2		
at $V_{CE} = 5 \text{ V}$ , $I_C = 10 \text{ mA}$ Collector-Emitter Cutoff Current at $V_{CE} = 80 \text{ V}$ BC546	V <sub>BE</sub>	- - -		15	nA
at $V_{CE} = 5 \text{ V}$ , $I_C = 10 \text{ mA}$ Collector-Emitter Cutoff Current at $V_{CE} = 80 \text{ V}$ at $V_{CE} = 50 \text{ V}$ BC546 BC547	V <sub>BE</sub> I <sub>CES</sub> I <sub>CES</sub>	- - - -	0.2	15 15	nA nA

<sup>1)</sup> Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



# BC546 THRU BC549

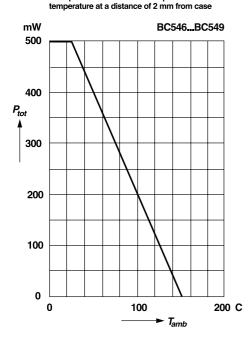
#### **ELECTRICAL CHARACTERISTICS**

Ratings at 25 °C ambient temperature unless otherwise specified

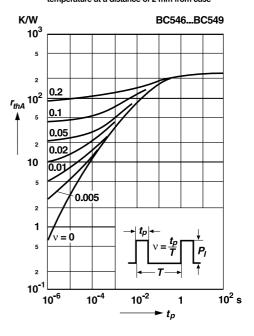
	Symbol	Min.	Тур.	Max.	Unit
at V <sub>CE</sub> = 30 V, T <sub>j</sub> = 125 °C <b>BC548</b> , <b>BC549</b>	I <sub>CES</sub>	-	-	4 4	μΑ μΑ
Gain-Bandwidth Product at $V_{CE}$ = 5 V, I <sub>C</sub> = 10 mA, f = 100 MHz	fT	-	300	_	MHz
Collector-Base Capacitance at $V_{CB}$ = 10 V, f = 1 MHz	C <sub>CBO</sub>	-	3.5	6	pF
Emitter-Base Capacitance at $V_{EB} = 0.5 V$ , f = 1 MHz	C <sub>EBO</sub>	_	9	_	pF
Noise Figure at V <sub>CE</sub> = 5 V, I <sub>C</sub> = 200 μA, R <sub>G</sub> = 2 kΩ, f = 1 kHz, Δf = 200 Hz <b>BC546, BC547</b>	F	_	2	10	dB
BC548 BC549	F	_	1.2	4	dB
at V <sub>CE</sub> = 5 V, I <sub>C</sub> = 200 μA, R <sub>G</sub> = 2 kΩ, f = 30…15000 Hz BC549	F	_	1.4	4	dB

## **RATINGS AND CHARACTERISTIC CURVES BC546 THRU BC549**

Admissible power dissipation versus temperature Valid provided that leads are kept at ambient



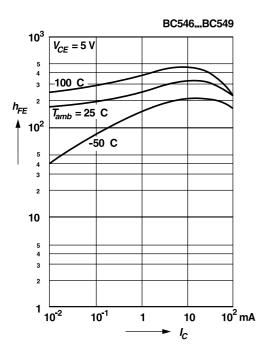
Pulse thermal resistance versus pulse duration Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



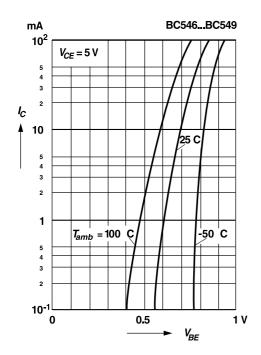
GENERAL SEMICONDUCTOR<sup>®</sup>

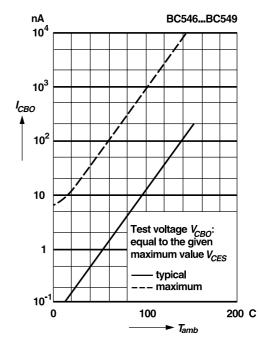
## **RATINGS AND CHARACTERISTIC CURVES BC546 THRU BC549**

DC current gain versus collector current

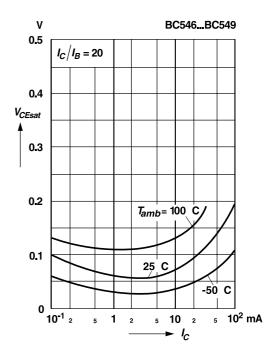


Collector current versus base-emitter voltage





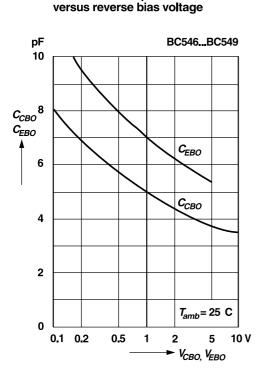
Collector saturation voltage versus collector current



GENERAL SEMICONDUCTOR<sup>®</sup>

Collector-base cutoff current versus ambient temperature

### **RATINGS AND CHARACTERISTIC CURVES BC546 THRU BC549**

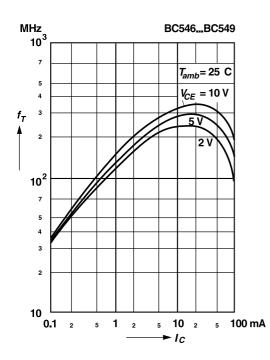


Collector-base capacitance,

**Emitter-base capacitance** 

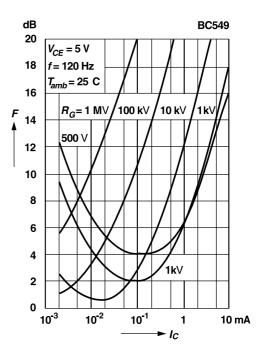
Gain-bandwidth product

versus collector current



BC546...BC549 10<sup>2</sup> 6 4  $h_e(I_C)$ 2  $h_e(I_C = 2 \text{ mA})$ 10 6 4 2 1 \_h<sub>fe</sub> 6 4 h<sub>oe</sub> 2  $V_{CE} = 5 \text{ V}$  $T_{amb} = 25$  C 10<sup>-1</sup> 10<sup>-1</sup> 1 10 mA 2 4 2 4 ► lc

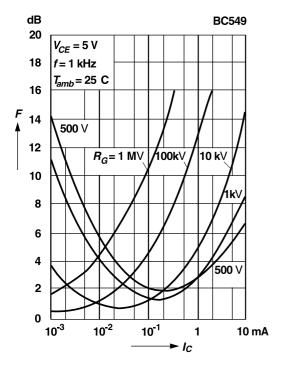
Noise figure versus collector current



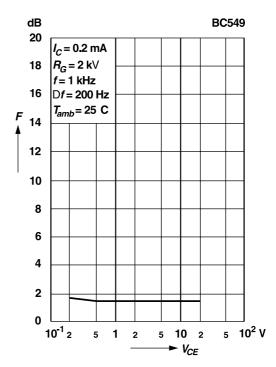
Relative h-parameters versus collector current

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## **RATINGS AND CHARACTERISTIC CURVES BC546 THRU BC549**



Noise figure versus collector current



Noise figure versus collector emitter voltage



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Datasheets for electronics components.